

The 38th RD50 Workshop (online Workshop)

Monday, 21 June 2021

SiC, Detector Characterization and Very High Fluence Experiments: Detector Characterization and Very High Fluence Experiments (13:55 - 17:00)

-Conveners: Eckhart Fretwurst

time	[id] title	presenter
13:55	[1] Time resolution of 4H-SiC PIN and simulation of 4H-SiC LGAD	Dr YANG, Tao
14:15	[57] Timing resolution simulation of 2D and 3D SiC devices	YUHANG, TAN TAN, Yuhang
14:35	[38] A new vision of I-V characteristics in irradiated Si sensors with heavily damaged regions	Dr VERBITSKAYA, Elena
14:55	[19] First results from thin silicon sensors irradiated to extreme fluence	SOLA, Valentina
15:15	Coffee Break	
15:30	[33] Performance of Stitched Passive CMOS Strip Sensors	BASELGA, Marta
15:50	[13] Full-size passive CMOS sensors for radiation tolerant hybrid pixel detectors	DIETER, Yannick Manuel
16:10	[10] Comparison studies of heavily irradiated dielectrics for AC-coupled pixel detectors on MCz silicon	BHARTHUAR, Shudhashil
16:30	[55] Discussion on High Fluences and Detector Characterization	CASSE, Gianluigi